

### POWER MANAGEMENT

#### Description

The SC1104A/B is a versatile voltage-mode PWM controller designed for use in single ended DC/DC power supply applications. A simple, fixed frequency high efficiency buck regulator can be implemented using the SC1104A/B with a minimum of external components. Internal level shift and drive circuitry eliminates the need for an expensive P-channel, high-side switch. The small device footprint allows for compact circuit design.

SC1104A/B features include temperature compensated voltage reference, triangle wave oscillator, current limit comparator and an externally compensated error amplifier. Current limit is implemented by sensing the voltage drop across the top FET's  $R_{DS(ON)}$ .

The SC1104 operates at fixed frequencies of 300kHz(A) or 600kHz(B) providing an optimum compromise between efficiency, external component size, and cost. 600kHz switching frequency is reserved for the SC1104B, +5V<sub>CC</sub> operation only.

SC1104A/B has a thermal protection circuit, which is activated if the junction temperature exceeds 150°C.

#### Typical Application Circuit

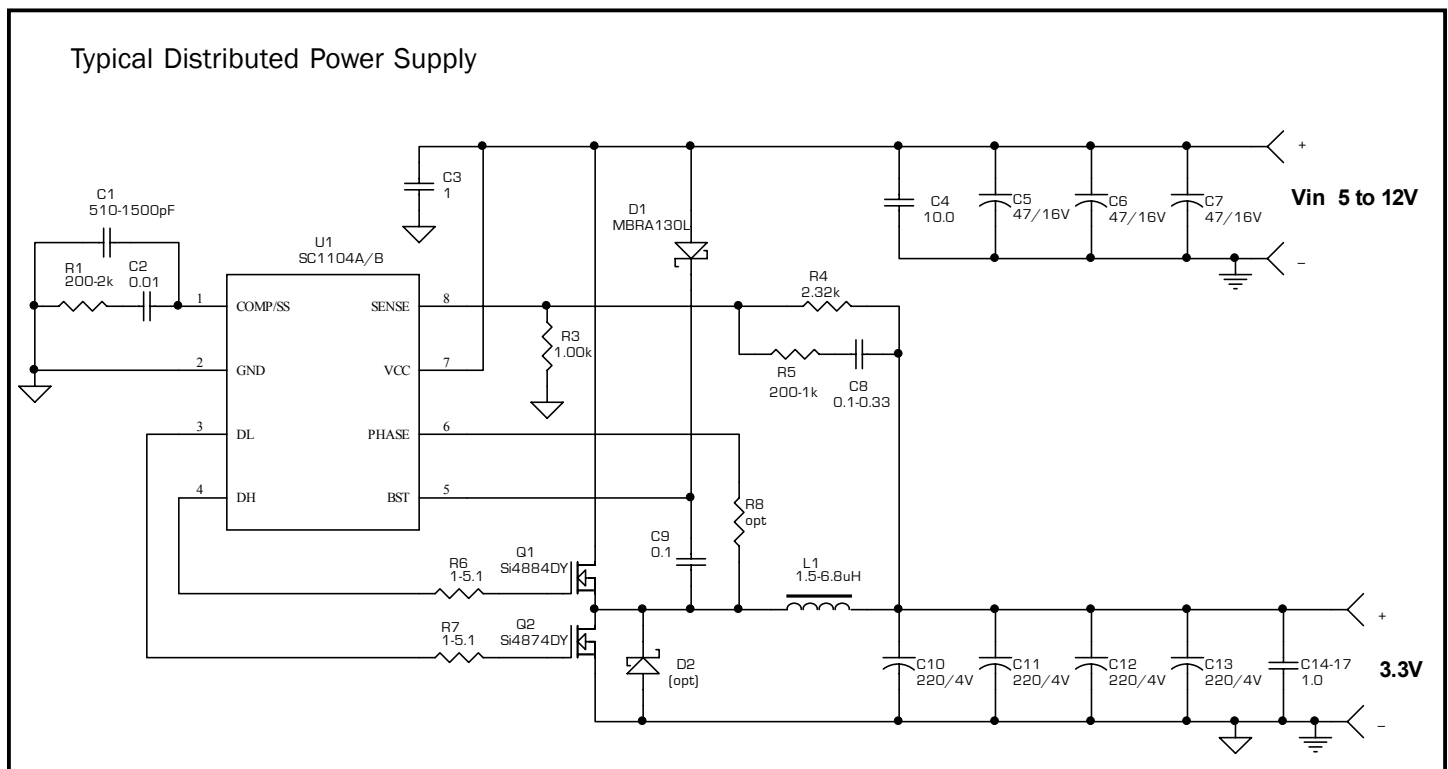


Figure 1

#### Features

- ◆ Up to +14V input, 300kHz operation (SC1104A)
- ◆ Up to +7V input, 600kHz operation (SC1104B)
- ◆ High efficiency (>90%)
- ◆ 1% Reference voltage accuracy
- ◆ Hiccup mode over current protection
- ◆ Robust output drive
- ◆  $R_{DS(ON)}$  Current sensing
- ◆ Industrial temperature range
- ◆ 8-Lead SOIC package. Pb-free package available, fully WEEE and RoHS compliant

#### Applications

- ◆ Termination supplies
- ◆ Low cost microprocessor supplies
- ◆ Peripheral card supplies
- ◆ Industrial power supplies
- ◆ High density DC/DC conversion

**POWER MANAGEMENT**
**Absolute Maximum Ratings**

Exceeding the specifications below may result in permanent damage to the device, or device malfunction. Operation outside of the parameters specified in the Electrical Characteristics section is not implied. Exposure to Absolute Maximum rated conditions for extended periods of time may affect device reliability.

Parameter	Symbol	Maximum	Units
V <sub>CC</sub> to GND		+20	V
BST to PHASE		+20	V
PHASE to GND		-0.5 to +20	V
COMP/SS to GND		+7	V
SENSE to GND		+7	V
Thermal Resistance Junction to Case	$\theta_{JC}$	40	°C/W
Thermal Resistance Junction to Ambient	$\theta_{JA}$	160	°C/W
Operating Junction Temperature Range	T <sub>J</sub>	-40 to +125	°C
Operating Ambient Temperature Range	T <sub>A</sub>	-40 to +85	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C
Lead Temperature (Soldering) 10 Sec.	T <sub>Lead</sub>	300	°C
ESD Rating (Human Body Model)	V <sub>ESD</sub>	2	kV

**Electrical Characteristics**

Unless specified: **A:** V<sub>CC</sub> = 12 ± 0.6V, V<sub>BST</sub> = 23 ± 1V, V<sub>OUT</sub> = 3.3V, T<sub>J</sub> = T<sub>A</sub> = 25°C. **B:** V<sub>CC</sub> = 5 ± 0.25V, V<sub>BST</sub> = 12 ± 0.6V, V<sub>OUT</sub> = 2.0V, T<sub>J</sub> = T<sub>A</sub> = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Power Supply</b>						
Supply Voltage	V <sub>CC</sub>	F <sub>SW</sub> = 300kHz (nom.), SC1104A	4.5		14	V
	V <sub>CC</sub>	F <sub>SW</sub> = 600kHz (nom.), SC1104B	4.5		7	
Supply Current	I <sub>CC</sub>	V <sub>COMP</sub> ≤ 0.4V		11	14	mA
<b>Error Amplifier</b>						
E/A Transconductance <sup>(1)</sup>	g <sub>m</sub>			12		mS
Open Loop DC Gain <sup>(1)</sup>	A <sub>O</sub>			42		dB
Bandwidth - 3dB <sup>(1)</sup>	F <sub>BW</sub>			400		kHz
Input Bias Current	I <sub>FB</sub>			1	3	μA
Output Sink Current	I <sub>SIK</sub>	V <sub>SENSE</sub> ≥ 1.1V; V <sub>COMP</sub> = 1.5V	0.65	0.7		mA
Source Current	I <sub>SC</sub>	V <sub>SENSE</sub> ≥ 0.9V; V <sub>COMP</sub> = 1.5V	0.95	1.1		
<b>Oscillator</b>						
Switching Frequency	F <sub>OSC</sub>	V <sub>CC</sub> = 12V ± 0.6V	255	300	345	kHz
		V <sub>CC</sub> = 5V ± 0.25V	510	600	690	

**POWER MANAGEMENT**
**Electrical Characteristics**

 Unless specified: **A:**  $V_{CC} = 12 \pm 0.6V$ ,  $V_{BST} = 23 \pm 1V$ ,  $V_{OUT} = 3.3V$ ,  $T_J = T_A = 25^\circ C$ . **B:**  $V_{CC} = 5 \pm 0.25V$ ,  $V_{BST} = 12 \pm 0.6V$ ,  $V_{OUT} = 2.0V$ ,  $T_J = T_A = 25^\circ C$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Ramp Peak Voltage <sup>(1)</sup>	$V_{P-K}$	$4.75V \leq V_{CC} \leq 12.6V$		2.0		V
Ramp Valley Voltage <sup>(1)</sup>	$V_V$	$4.75V \leq V_{CC} \leq 12.6V$		1.0		V
Maximum Duty Cycle <sup>(2)</sup>	$dc_{MAX}$	$V_{CC} = 12V$ (300kHz, SC1104A)	90	95		%
		$V_{CC} = 5V$ (600kHz, SC1104B)	85	90		
<b>MOSFET Drivers</b>						
DH Sink/Source Current SC1104A	$I_{DH}$	d.c. < 2%, $t_{PW} < 100\mu s$ $V_{GS} = 4.5V$ (src)	0.6	0.8		A
DL Sink/Source Current SC1104A	$I_{DL}$	$V_{GS} = 2.5V$ (snk)	0.6	0.7		
DH Sink/Source Current SC1104B	$I_{DH}$	d.c. < 2%, $t_{PW} < 100\mu s$ $V_{GS} = 4.5V$ (src)	0.45	0.6		A
DL Sink/Source Current SC1104B	$I_{DL}$	$V_{GS} = 2.5V$ (snk)	0.45	0.6		
DH Rise/Fall Time	$t_r, t_f$	$C_L = 3000pF$ , See Fig. 2		50		ns
DL Rise/Fall Time	$t_r, t_f$	$C_L = 4000pF$ , See Fig. 2		50		
Dead Time	$t_{dt}$	See Fig. 2		80		ns
DH Minimum Off Time	$t_{OFF}$	$4.75V \leq V_{CC} \leq 12.6V$		160		
<b>Reference Section</b>						
Reference Voltage	$V_{REF}$	$4.75V \leq V_{CC} \leq 12.6V$	0.990	1.000	1.010	V
Temp Variance	$\Delta V_{REF}$	$0 < T_J < +70^\circ C$	-1		1	%
		$-40 < T_J < +85^\circ C$	-1.5		1.5	
Long Term Stability		$T_J = 125^\circ C$ , 1000 hrs.			5	mV
<b>Current Limit</b>						
Trip Voltage	$V_{TRIP}$	$4.75V < V_{CC} < 12.6V$ $V_{trp} = V_{CC} - V_{PHASE}$	180	200	220	mV
<b>Soft-Start/Enable</b>						
SS Source Current	$I_{SRC}$	$V_{COMP} < 2.5V$	0.5		1.8	$\mu A$
SS Sink Current	$I_{SNK}$	$V_{COMP} > 0.5V$	0.5		1.8	$\mu A$
Enable Input Threshold			1.00		1.35	V
Enable Input Current		$V_{COMP} = 0.8V$			2	mA

**POWER MANAGEMENT**

**Electrical Characteristics**

Unless specified: **A:**  $V_{CC} = 12 \pm 0.6V$ ,  $V_{BST} = 23 \pm 1V$ ,  $V_{OUT} = 3.3V$ ,  $T_J = T_A = 25^\circ C$ . **B:**  $V_{CC} = 5 \pm 0.25V$ ,  $V_{BST} = 12 \pm 0.6V$ ,  $V_{OUT} = 2.0V$ ,  $T_J = T_A = 25^\circ C$

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Under Voltage Lockout</b>						
UVLO Threshold	$V_{th}$	$-40 < T_J < 85^\circ C$	3.9	4.15	4.5	V
<b>Thermal Shutdown</b>						
Over Temperature Trip Point <sup>(2)</sup>	$T_{OTP}$		140		160	$^\circ C$

Notes:

- (1) Guaranteed by design.
- (2) Not tested, by characterization.

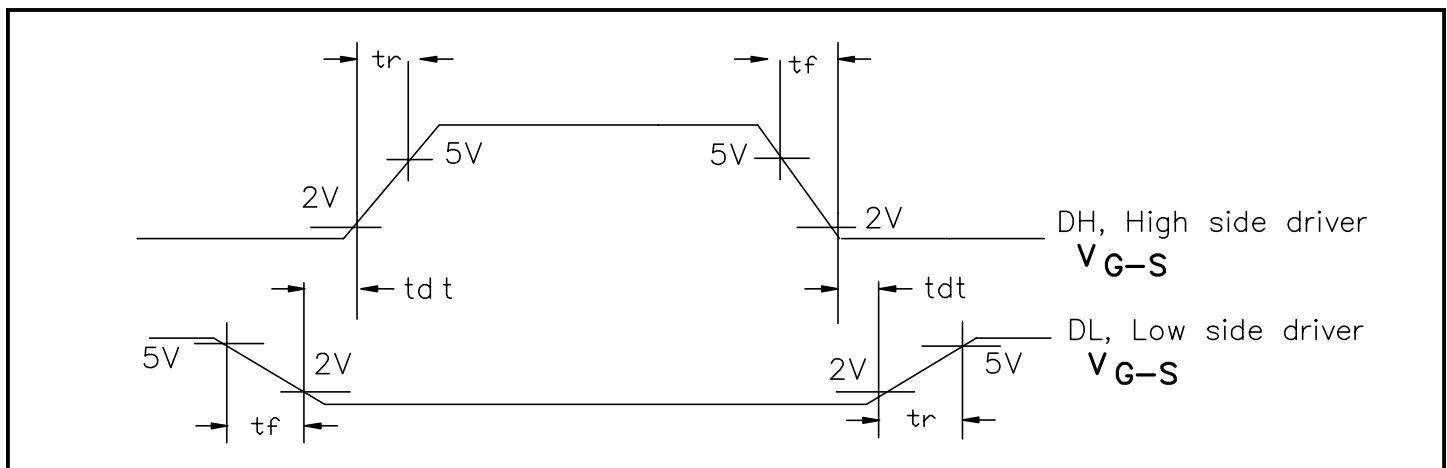


Figure 2

**Block Diagram**

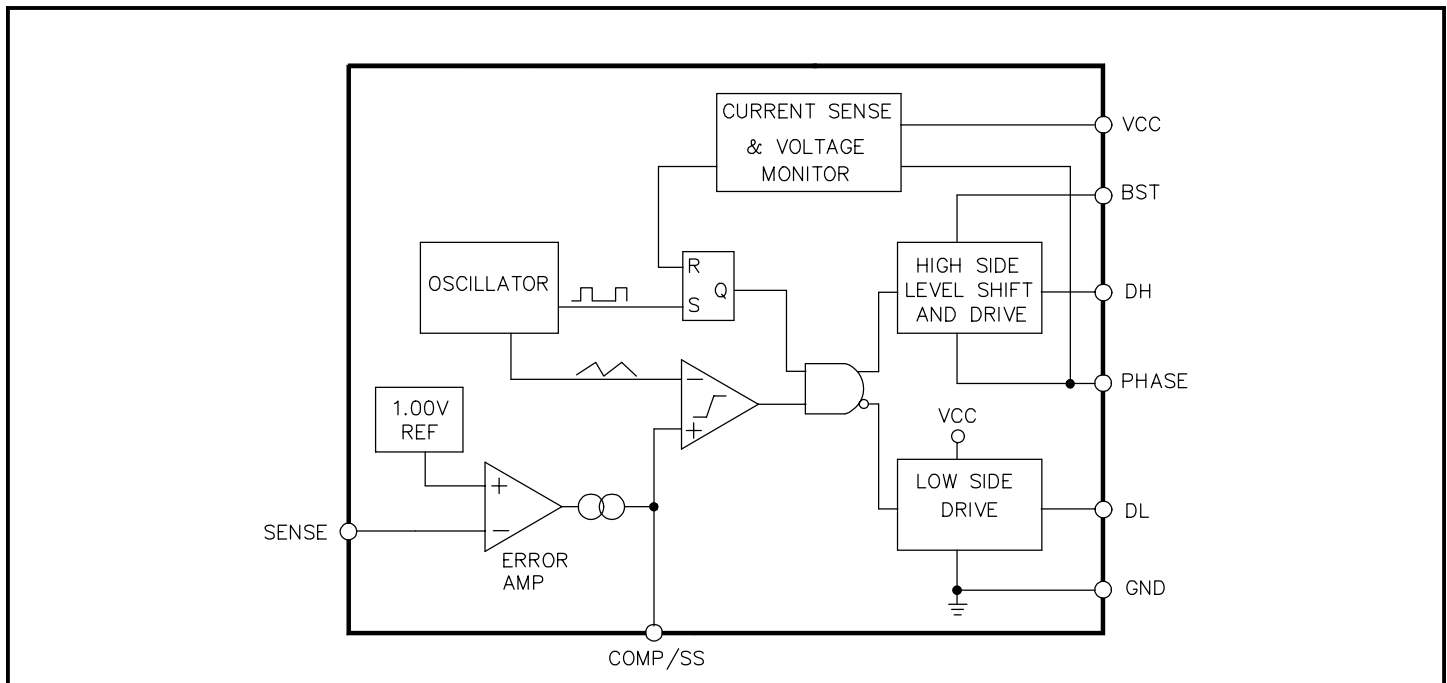
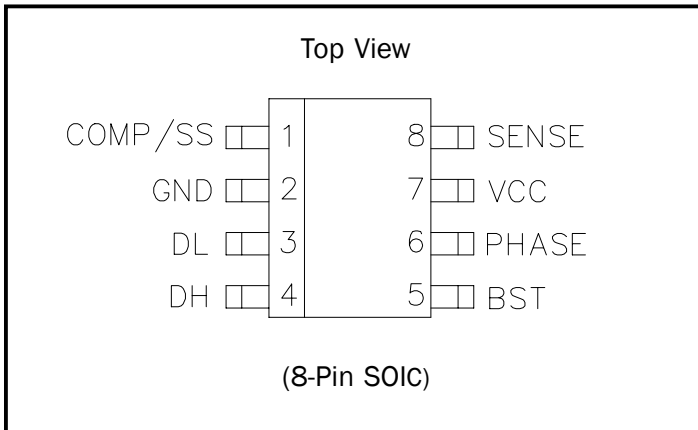


Figure 3

## POWER MANAGEMENT

### Pin Configuration



### Ordering Information

Device <sup>(2)</sup>	Package	Temp Range (T <sub>j</sub> )
SC1104XISTR <sup>(1)</sup>	SOIC-8	-40° to 125°C
SC1104XISTR <sup>(1)(3)</sup>		
SC1104XEVB	Evaluation Board	

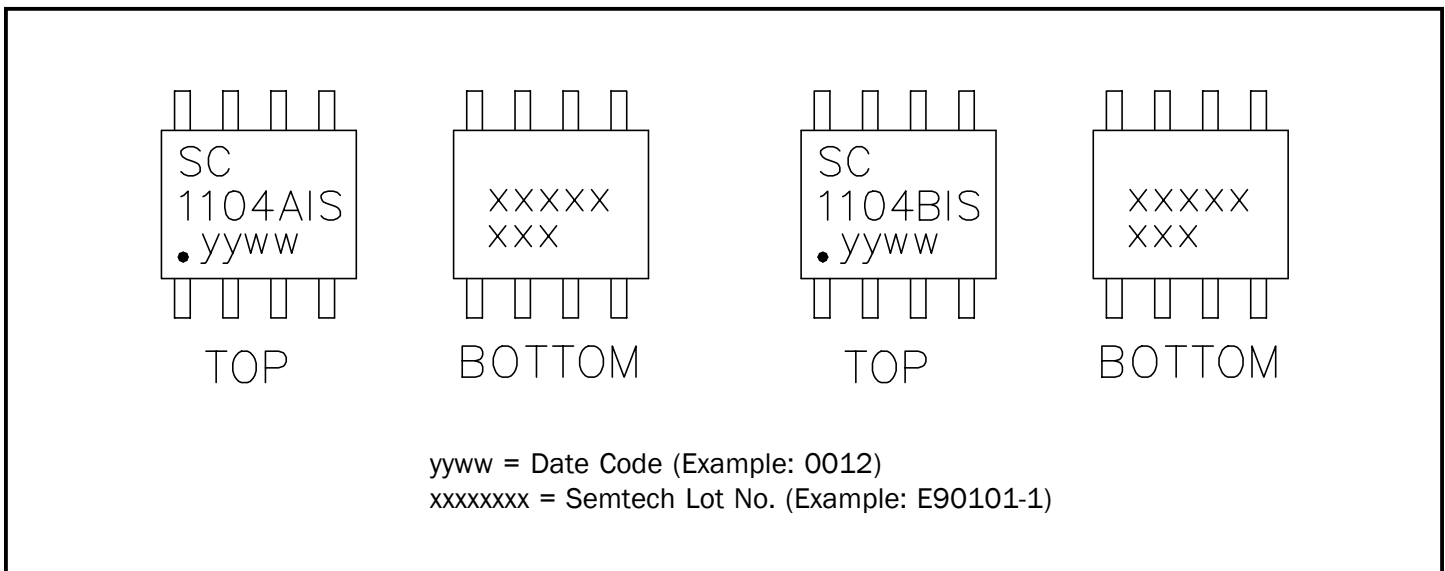
#### Notes:

- (1) In place of "X": A = 300kHz, V<sub>CC</sub> = 5V to 12V.  
B = 600kHz, V<sub>CC</sub> = 5V.
- (2) Only available in tape and reel packaging. A reel contains 2500 devices.
- (3) Lead free product. This product is fully WEEE and RoHS compliant.

### Pin Descriptions

Pin #	Pin Name	Pin Function
1	COMP/SS	Error amplifier output. Compensation, soft start/enable.
2	GND	Ground.
3	DL	Low side driver output
4	DH	High side driver output
5	BST	Bootstrap, high side driver.
6	PHASE	Input from the phase node between the MOSFETs.
7	VCC	Chip bias supply voltage.
8	SENSE	Output voltage sense input.

### Marking Information



**POWER MANAGEMENT**
**Theory of Operation**
**Synchronous Buck Converter**

The output voltage of the synchronous converter is set and controlled by the output of the error amplifier. The inverting input of the error amplifier receives its voltage from the SENSE pin. The non-inverting input of the error amplifier is connected to an internal 1V reference.

The error amplifier output is connected to the COMPensation pin. The error amplifier generates a current proportional to  $(V_{sense} - 1V)$ , which is the COMP pin output current (Transconductance  $\sim 12mS$ ). The voltage on the COMP pin is the integral of the error amplifier current. The COMP voltage is the non-inverting input to the PWM comparator and controls the duty cycle of the MOSFET drivers. The size of capacitor  $C_{comp}$  controls the stability and transient response of the regulator. The larger the capacitor, the slower the COMP voltage changes, and the slower the duty cycle changes.

The inverting input voltage of the PWM comparator is the triangular output of the oscillator.

When the oscillator output voltage drops below the COMP voltage, the comparator output goes high. This pulls DL low, turning off the low-side FET. After a short delay ("dead time"), DH is pulled high, turning on the high-side FET. When the oscillator voltage rises back above the error amplifier output voltage, the comparator output goes low. This pulls DH low, turning off the high-side FET, and after a dead time delay, DL is pulled high, turning on the low-side FET. The dead time delay is determined by a monostable on the chip.

The triangle wave minimum is about 1V, and the maximum is about 2V. Thus, if  $V_{comp} = 0.9V$ , high side duty cycle is the minimum ( $\sim 0\%$ ), but if  $V_{comp}$  is 2.0V, duty cycle is at maximum ( $\sim 90\%$ ). The internal oscillator uses an on-chip capacitor and trimmed precision current sources to set the oscillation frequency to 300kHz (SC1104A) or 600kHz (SC1104B).

Figure 1 shows a 3.3V output converter. If the  $V_{out} < 3.3V$ , then the SENSE voltage  $< 1V$ . In this case the error amplifier will be sourcing current into the COMP pin so that COMP voltage and duty cycle will gradually increase. If  $V_{out} > 3.3V$ , the error amplifier will sink current and reduce the COMP voltage, so that duty cycle will decrease.

The circuit will be in steady state when  $V_{out} = 3.3V$ ,  $V_{sense} = 1V$ ,  $I_{comp} = 0$ . The COMP voltage and duty cycle depend on  $V_{in}$ .

**Under Voltage Lockout**

The under voltage lockout circuit of the SC1104A/B assures that both high-side and low-side MOSFET driver outputs remain in the off state whenever the supply voltage drops below set parameters. Lockout occurs if  $V_{cc}$  falls below 4.2V typ.

 **$R_{DS(ON)}$  Current Limiting**

In case of a short circuit or overload, the high-side (HS) FET will conduct large currents. To prevent damage, in this situation, large currents will generate a fault condition and begin a soft start cycle.

While the HS driver is on, the phase voltage is compared to the  $V_{cc}$  pin voltage. If the phase voltage is 200mV lower than  $V_{cc}$ , a fault is latched and the soft start cycle begins.

The voltages are compared during the middle of the HS pulse, to prevent transients from affecting the accuracy.

The sampling of the voltage across the top FET occurs after a time delay  $t_{DELAY} = 100ns_{typ}$  from the time the DH is pulled high. This delay prevents the measurement to be effected by ringing on the leading edge of the phase node pulse. The duration of the sampling is  $t_{SAMPLE} = 100ns_{typ}$ . It is being disabled at very low duty cycle when  $t_{ON} < 300ns_{typ}$ . This feature allows for the orderly start-up during the inrush of the current charging output capacitor and the fault free operation with extremely high input/output voltage ratio, e.g.,  $V_{IN} = 12V$  and  $V_{OUT} = 1V$ .

The over-current comparator (OC) is only active if the phase node is  $> 3.3V$ . This means that in the case of power source being  $< 3V$  the OC will be disabled even though the rest of the circuitry is completely functional. SC1104 still can be used for stepping down, e.g. 2.8V to 2.5V, 2V, 1.8V, etc.

**POWER MANAGEMENT**
**Theory of Operation (Cont.)**

When choosing OC trip point one should consider the Tempco of the MOSFETs  $R_{ds\_on}$  and SC1104's  $V_{trip}$ . Also, any ringing on the  $V_{cc}$  and Phase nodes due to parasitic L and C will have some effect on the OC  $V_{trip}$ .

**Example:**

$I_{out\_nom} = 6A$ ; assume  $I_{max} = 125\% \cdot I_{out\_nom} = 7.5A$

$R_{ds\_on} = 0.014\Omega$ ; assume  $R_{ds\_on\_max} \approx 150\% \cdot R_{ds\_on} = 0.02\Omega$

$V_{oc} = 7.5A \cdot 0.02\Omega = 150mV$ .

This proves that MOSFETs with  $R_{DS\_ON} = 0.014\Omega @ 25^\circ C$  is the right choice.

**Soft Start**

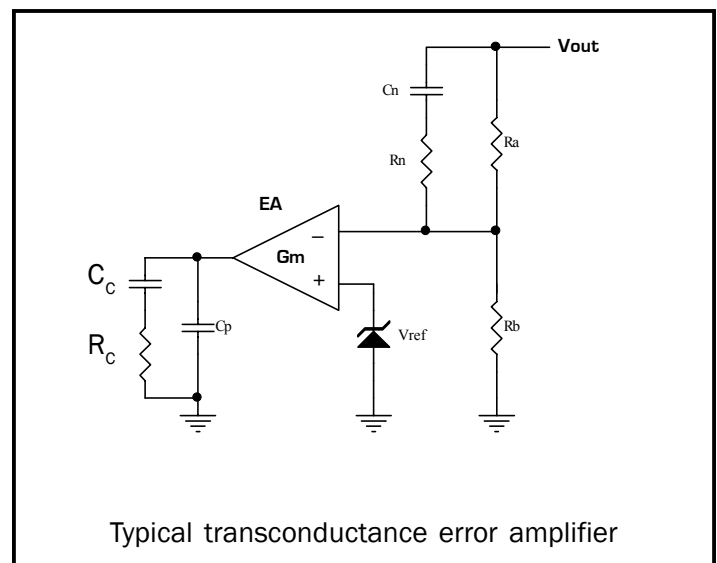
The soft start (or hiccup) circuitry is activated when a fault occurs. Faults occur for three reasons:

- 1) Under voltage ( $V_{cc} < 4.2V$ )
- 2) Over temperature (die temperature  $> 150^\circ C$ )
- 3) Over current in high side FET.

All faults are handled the same way. Both DH and DL are forced low. The error amplifier is turned off, but a  $2\mu A$  current flows into the comp pin (soft start current). The sink current reduces the Comp voltage down to  $0.6V$  over a period of a few milliseconds. When  $V_{comp} \sim 0.6V$ , the fault is cleared and the DL goes high. Also, the soft start current changes polarity and begins to increase the voltage on the Comp capacitor. The DH remains low, because  $V_{comp}$  is less than the lowest excursion of the oscillator ramp ( $1.0V$ ). After a few ms, the  $V_{comp}$  increases to about  $1.0V$  and the DH will start to switch. The duty cycle will gradually increase, and  $V_{sns}$  will increase. When  $V_{sns} \sim 1.00V$ , the error amplifier turns on again. The circuit has now reached its operating point. If a fault occurs during the soft start, the cycle will begin again (drivers low,  $V_{comp}$  decreasing down to  $0.6V$ ).

**Closing the Loop**

In order to have a stable closed loop system with optimum transient response one should make sure that open-loop frequency response has an adequate Gain & Phase margins. The Bode plot of log. Gain vs Freq. and Phase vs Freq. provide the necessary means for the circuit evaluation. Loop stability defined by compensation networks around transconductance error amplifier (EA) and output divider, see below and output capacitor  $C_{out}$  and inductor  $L_{out}$ .



The inductor and output capacitor form a “double pole” at the frequency:

$$f_{LC} = \frac{1}{2 \cdot \pi \cdot \sqrt{L_o \cdot C_o}}$$

The ESR of the output capacitor and the output capacitor value create a “zero” at the frequency.

$$f_{ESR} = \frac{1}{2 \cdot \pi \cdot ESR \cdot C_o}$$

The “zero” and “pole” from the EA compensation network are:

$$f_z = \frac{1}{2 \cdot \pi \cdot R_c \cdot C_c} \quad f_p = \frac{1}{2 \cdot \pi \cdot R_c \cdot C_p}$$

The additional “lead” network  $R_A, C_N, R_N$  can be used to improve phase margin in case when output capacitors with extra-low ESR are used and there is a need to compensate for “high quality” output  $L_o, C_o$  filter.

**POWER MANAGEMENT**
**Theory of Operation (Cont.)**

$$f_{NET} = \frac{1}{2 \cdot \Pi \cdot R_A \cdot C_N}$$

Value for the resistor  $R_N$  should be 1/10 of the output divider upper resistor  $R_A$ .

Example.

Switching frequency  $f_{SW} = 300\text{kHz}$

Output capacitance  $C_{OUT} = 3 \times 330\mu\text{F}$

Output capacitor ESR = 45mΩ/each

Output inductance  $L_{OUT} = 4.7\mu\text{H}$

Input voltage  $V_{IN} = 12\text{V}$

Output voltage  $V_{OUT} = 3.3\text{V}$

Let's choose crossover frequency

$$f_{CO} = 1/20 \cdot f_{SW} = 15\text{kHz}$$

The compensation values used in this example are based on the following criteria:

$$f_z = f_{LC}; f_{NET} = 1/10 \cdot f_{LC}; f_p = 10 \cdot f_{CO} = 150\text{kHz}$$

Therefore,

$$f_{LC} = \frac{1}{2 \cdot \Pi \cdot \sqrt{4.7\mu\text{H} \cdot 990\mu\text{F}}} = 2.33\text{kHz}$$

$$f_{ESR} = \frac{1}{2 \cdot \Pi \cdot 0.015 \cdot 990\mu\text{F}} = 10.72\text{kHz}$$

Since, the EA can sink/source about 1mA, let's choose  $R_C = 680\Omega$ , then

$$C_C = \frac{1}{2 \cdot \Pi \cdot F_z \cdot R_C} = 0.1\mu\text{F}$$

$$C_P = \frac{1}{2 \cdot \Pi \cdot F_p \cdot R_C} = 1500\text{pF}$$

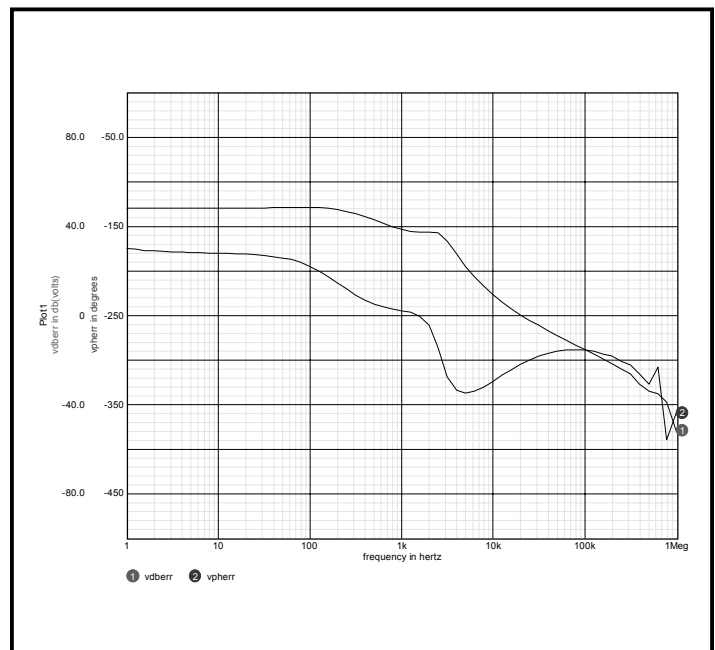
Assuming the output divider lower resistor  $R_B = 1\text{k}$ , then for  $V_{OUT} = 3.3\text{V}$  the  $R_A = 2.32\text{k}$ .

$$C_N = \frac{1}{2 \cdot \Pi \cdot f_{NET} \cdot R_A} = 0.3\mu\text{F}$$

At the closed-loop crossover frequency  $f_{CO}$ , the

attenuation due to the  $L_O$ ,  $C_O$  filter and the output resistor divider  $R_A$ ,  $R_B$  is compensated by the gain of the PWM modulator and the gain of the transconductance error amplifier ( $G_{m_{EA}} \cdot Z_{COMP}$ ).

Shown below is a typical Bode plot of the open-loop frequency response of SC1104 based buck converter.

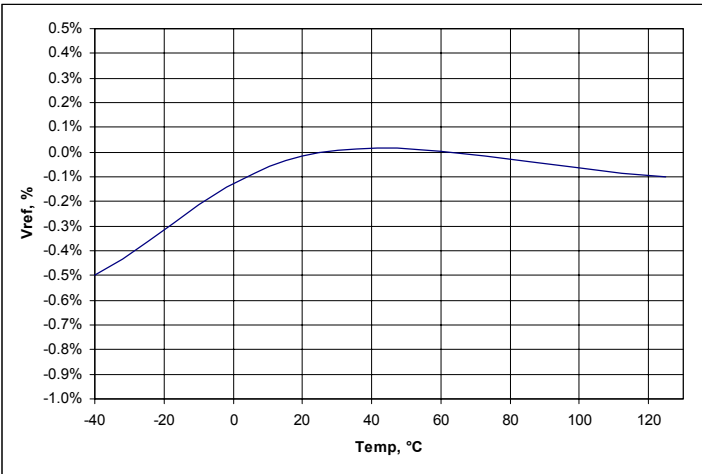




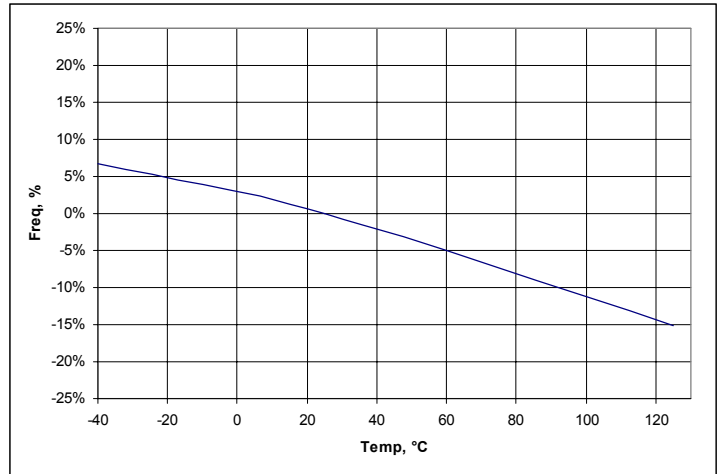
POWER MANAGEMENT

Typical Characteristics

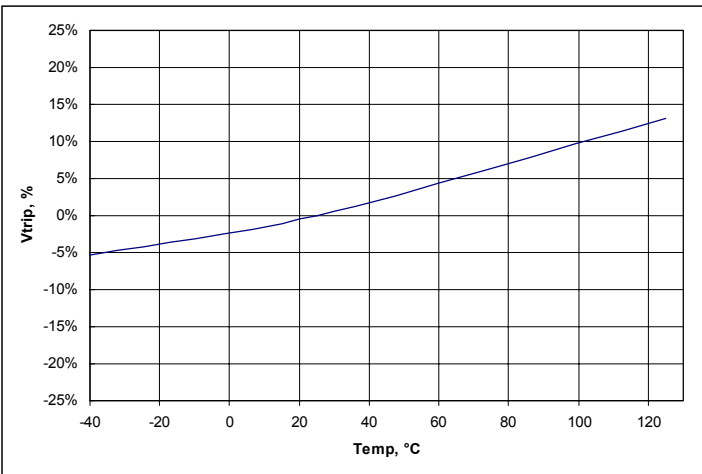
Reference Voltage vs. Temp



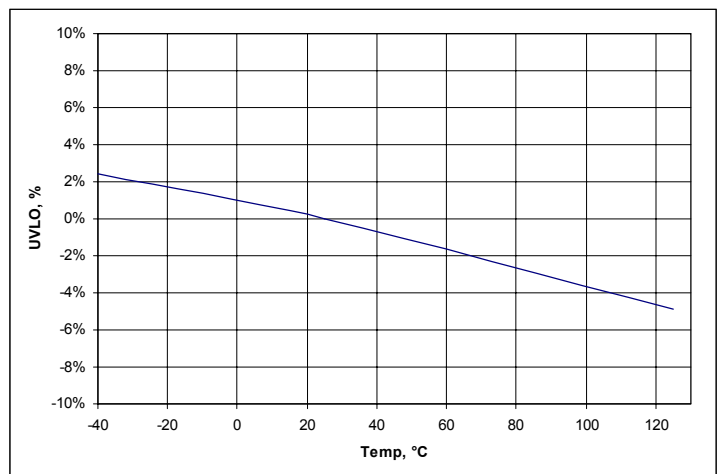
Switching Frequency vs. Temp



Trip Voltage vs. Temp

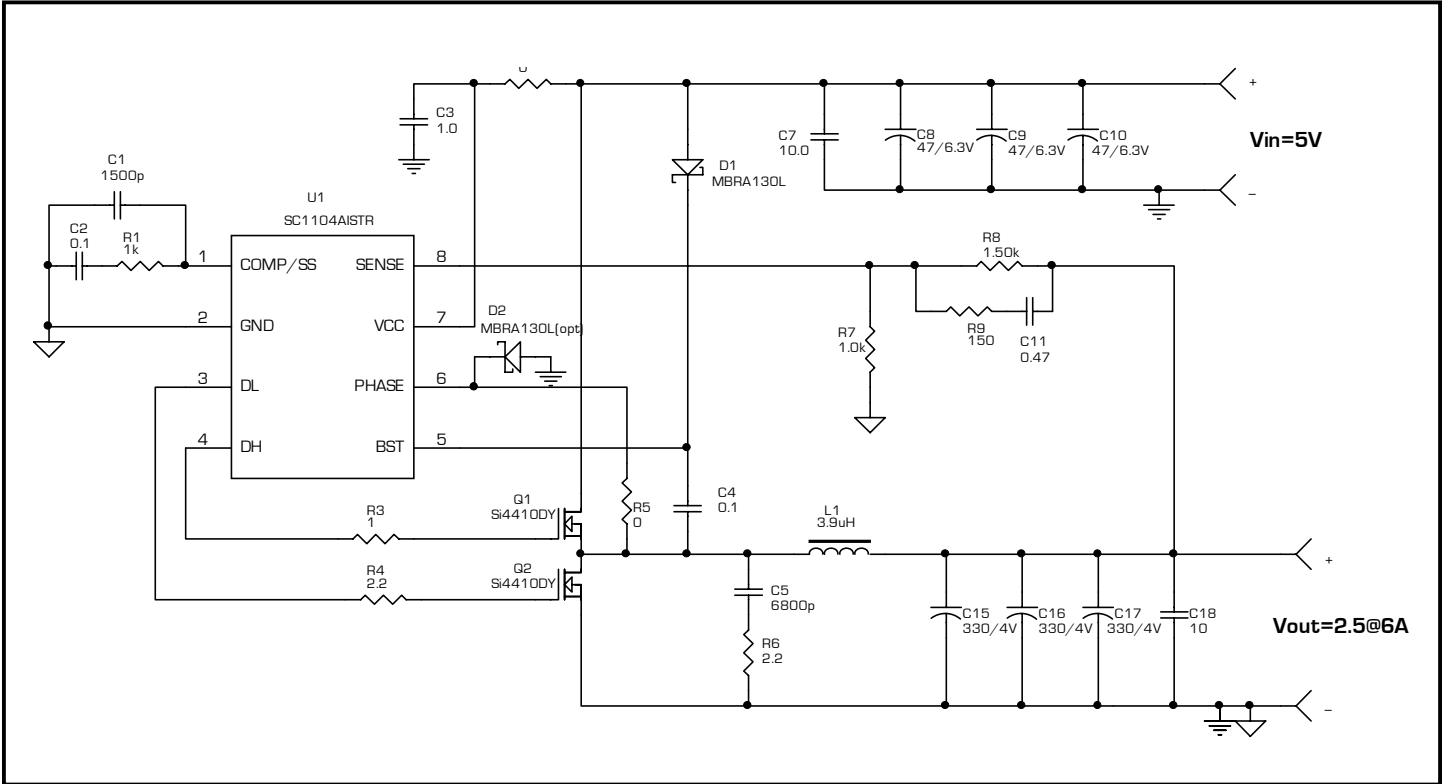


Under Voltage Lockout vs. Temp

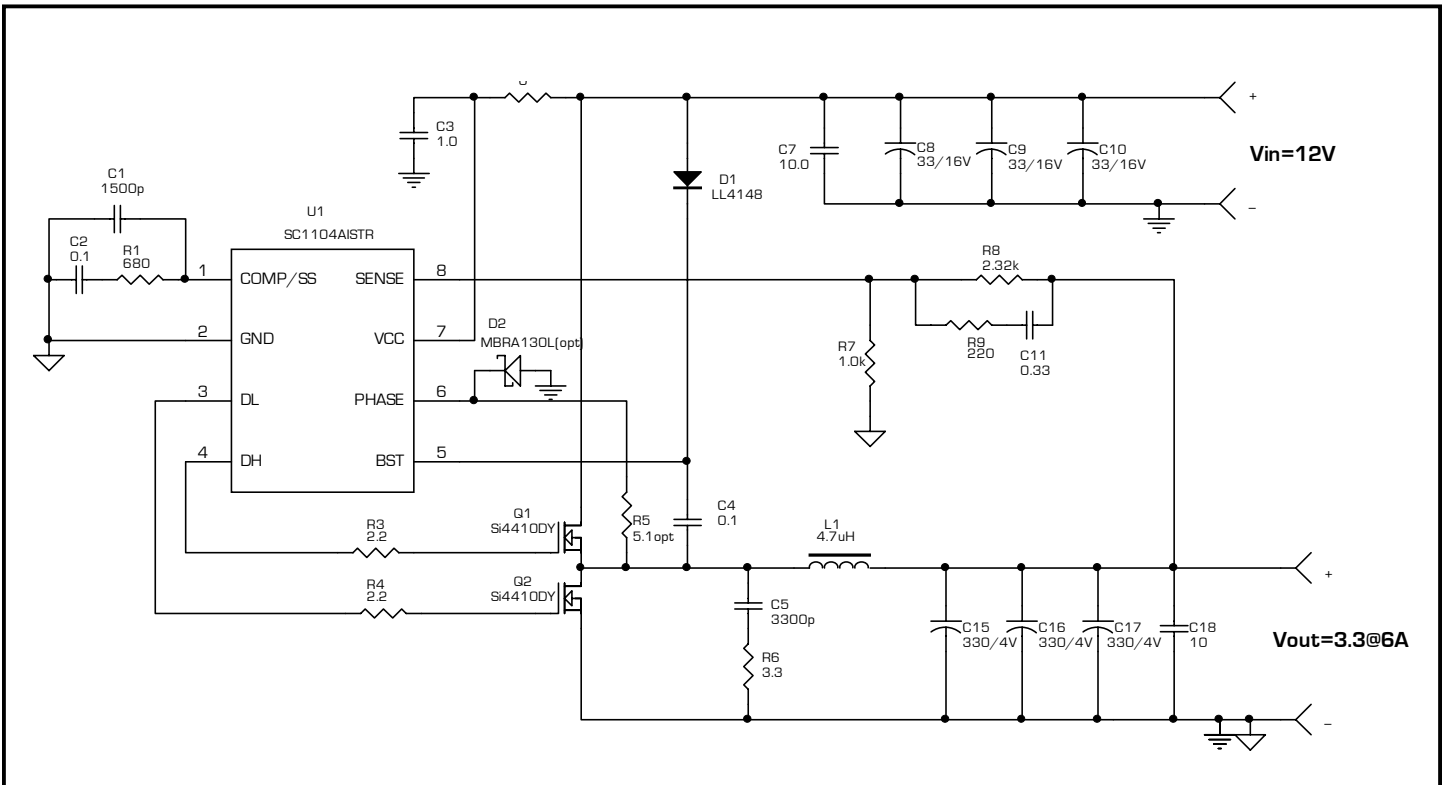


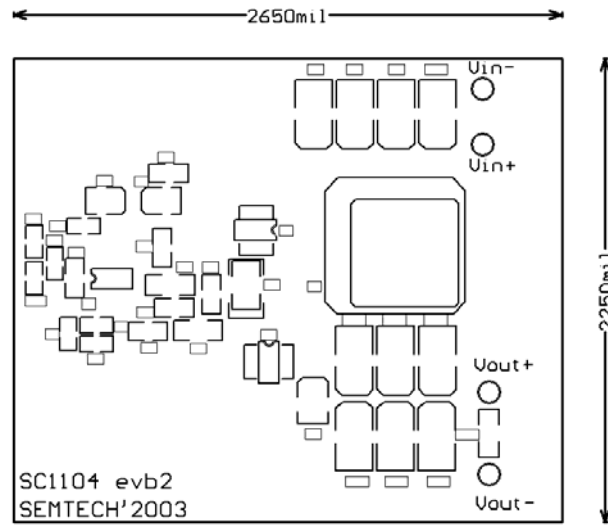
**POWER MANAGEMENT**

**Evaluation Board Schematic -  $V_{IN} = 5V$**

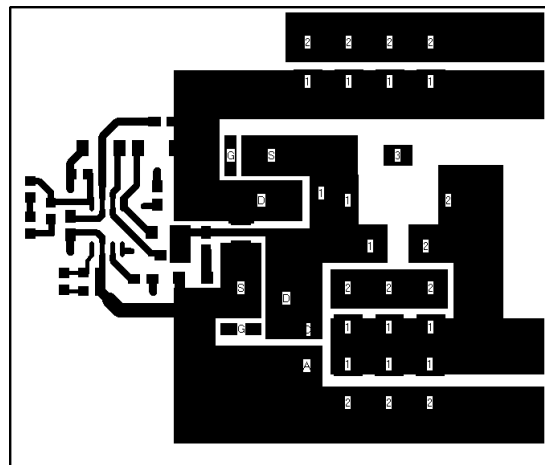


**Evaluation Board Schematic -  $V_{IN} = 12V$**

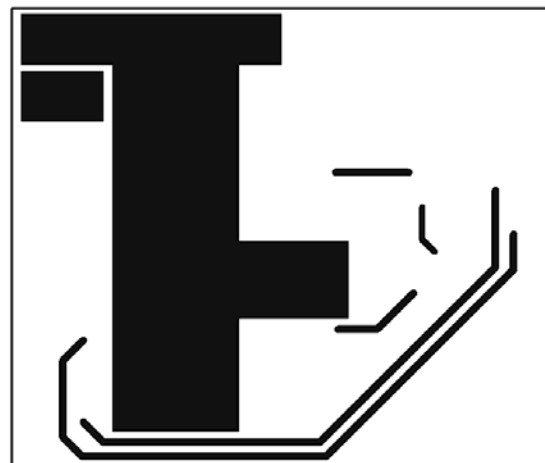


**POWER MANAGEMENT**
**Evaluation PC Board**


Top View



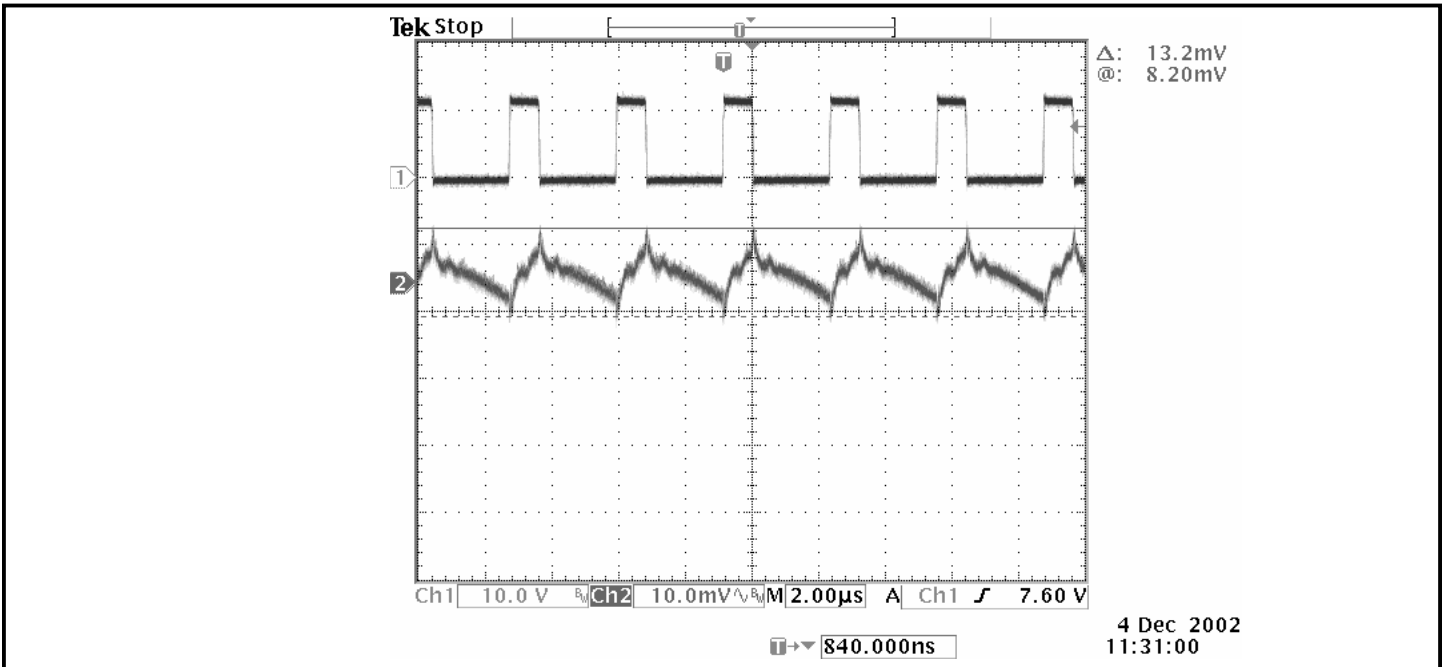
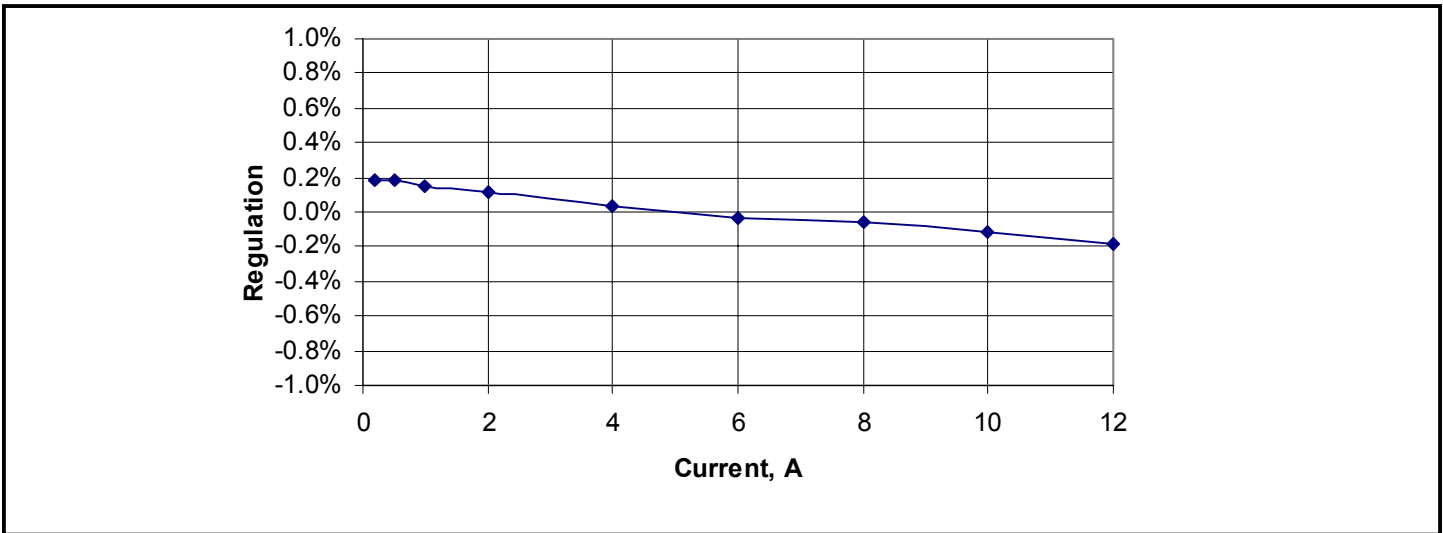
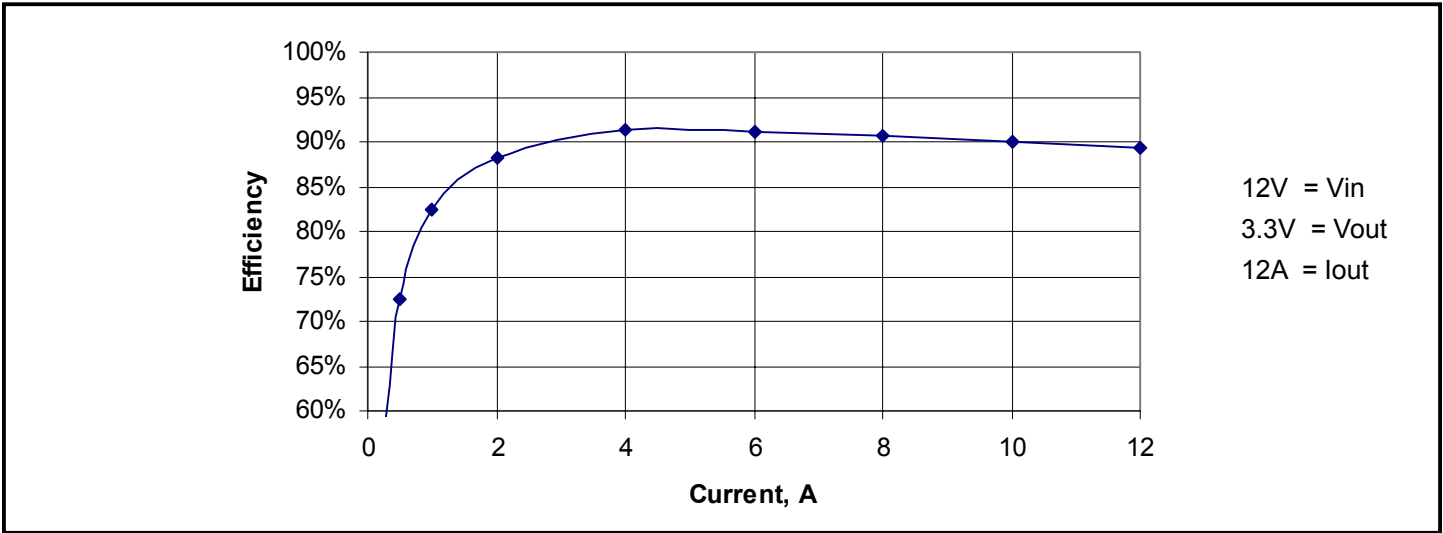
Top Layer



Bottom Layer

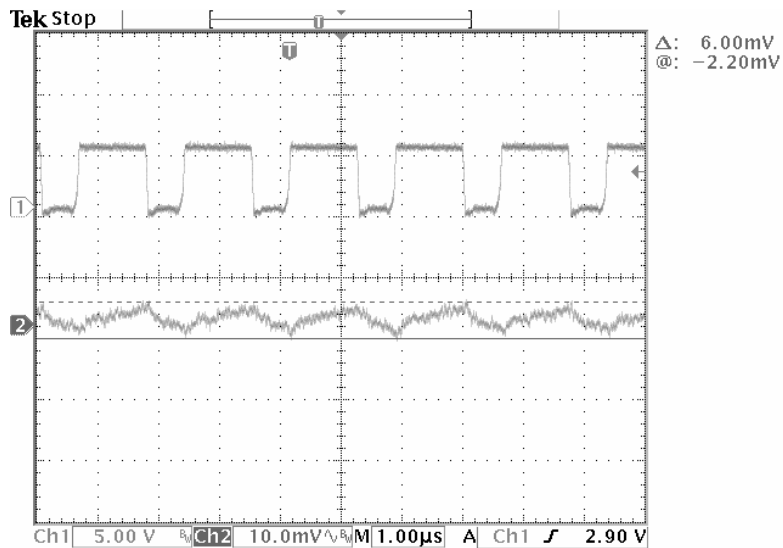
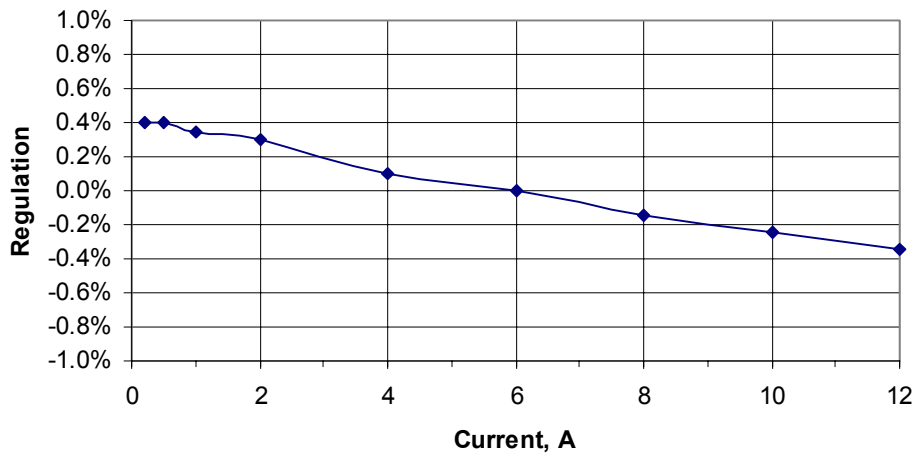
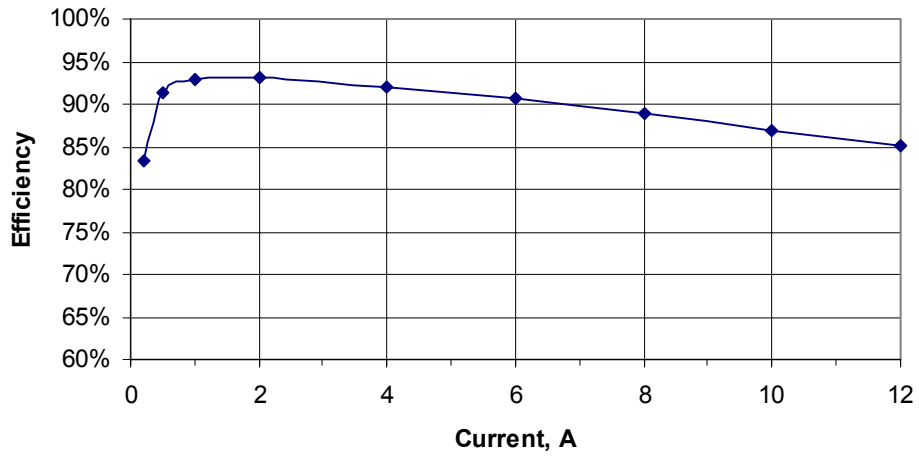
POWER MANAGEMENT

Typical Characteristics



POWER MANAGEMENT

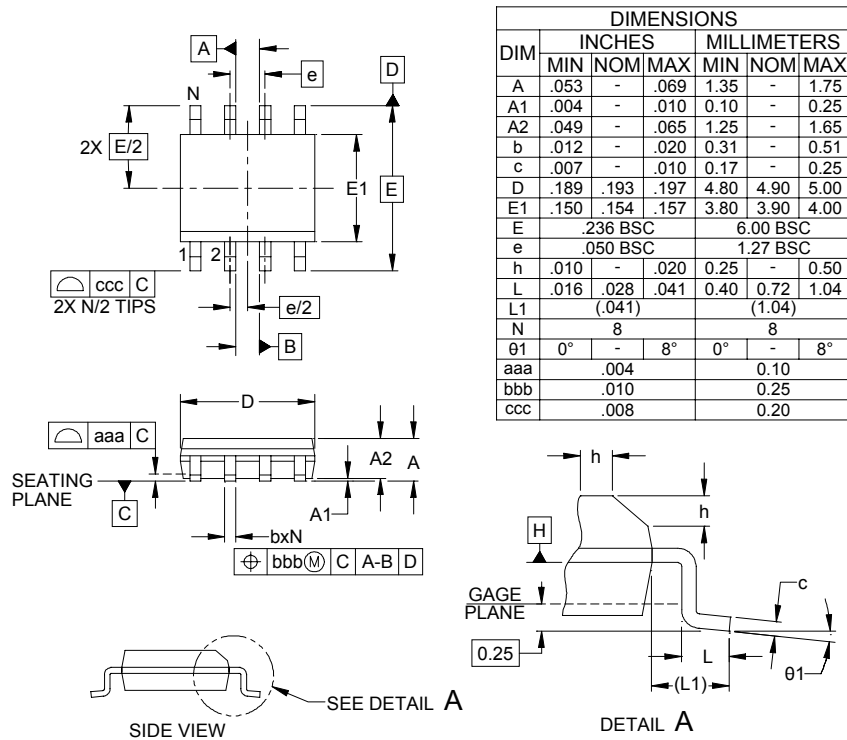
Typical Characteristics (Cont.)



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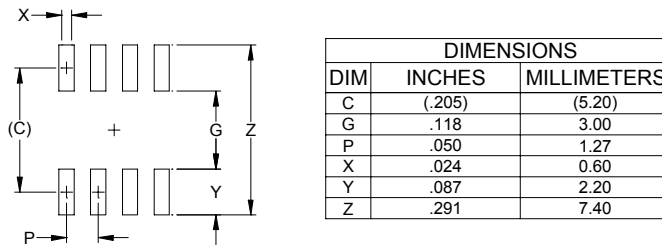
**POWER MANAGEMENT**

**Outline Drawing - SOIC - 8**



- NOTES:
1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
  2. DATUMS **-A-** AND **-B-** TO BE DETERMINED AT DATUM PLANE **-H-**
  3. DIMENSIONS "E1" AND "D" DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
  4. REFERENCE JEDEC STD MS-012, VARIATION AA.

**Minimum Land Pattern - SOIC - 8**



- NOTES:
1. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.
  2. REFERENCE IPC-SM-782A, RLP NO. 300A.

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